

WP7113PD1C

Photodiode

DESCRIPTION

• Made with silicon phototransistor chips

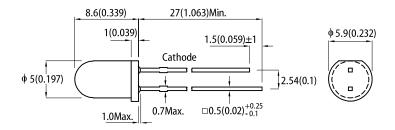
FEATURES

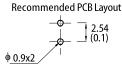
- · Mechanically and spectrally matched to the infrared emitting LED lamp
- · RoHS compliant

APPLICATIONS

- · Infrared applied systems
- · Optoelectronic switches
- · Photodetector control circuits
- Sensor technology

PACKAGE DIMENSIONS





- Notes:

 1. All dimensions are in millimeters (inches).
 2. Tolerance is ±0.25(0.01") unless otherwise noted.
 3. Lead spacing is measured where the leads emerge from the package.
 4. The specifications, characteristics and technical data described in the datasheet are subject to change

ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Max.Ratings	Units			
Power Dissipation	150	mW			
Operating Temperature	-40 to +85	°C			
Storage Temperature	-40 to +85	°C			
Lead Soldering Temperature [1]	260°C For 3 Seconds				
Lead Soldering Temperature [2]	260°C For 5 Seconds				

^{1.2}mm below package base.
2.5mm below package base.
3. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

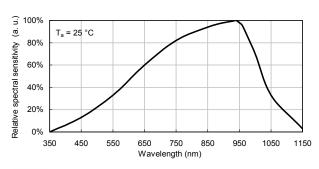


ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

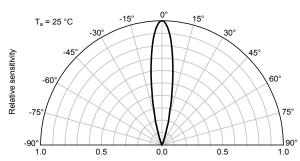
Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Reverse Break down Voltage	V _{(BR)R}	33	170	-	V	$I_R = 100uA$ $H = 0mW/cm^2$
Reverse Dark Current	ID _(R)	-	-	10	nA	$V_R = 10V$ H = 0mW/cm ²
Open Circuit Voltage	V _{oc}	-	390	-	mV	$\lambda = 940 \text{nm}$ $H = 5 \text{mW/cm}^2$
Rise Time	T _R	-	6	-	nS	$V_R = 10V$ $\lambda = 940$ nm $R_L = 1000\Omega$
Fall Time	T _F	-	6	-	nS	
Light current	Is	0.1	0.4	-	uA	$V_R = 5V$ Ee = 0.08mW/cm ² $\lambda = 940$ nm
Total Capacitance	Ст	-	5	-	pF	$V_R = 10V$ $F = 1MHZ$ $H = 0mW/cm^2$
Range of spectral bandwidth	λ _{0.1}	420	-	1120	nm	-
Wavelength of peak sensitivity	λ_{p}	-	940	-	nm	-
Angle of half sensitivity	201/2	-	20	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH



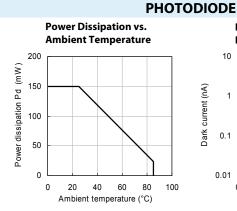
RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

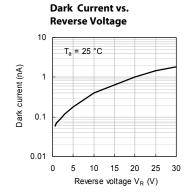


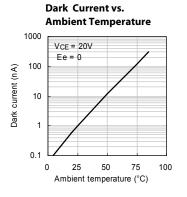


TECHNICAL DATA

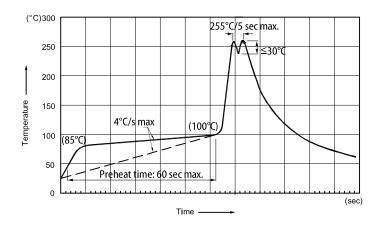
Light Current vs. Irradiance 100 V_P=5V T_a = 25 °C -ight current Is (µA) 0.01 10 100 1000 10000 Irradiance Ee (µW/cm²)







RECOMMENDED WAVE SOLDERING PROFILE



Notes:

- Recommend pre-heat temperature of 105°C or less (as measured with a thermocouple attached to the LED pins) prior to immersion in the solder wave with a maximum solder bath
- temperature of 260°C

 2. Peak wave soldering temperature between 245°C ~ 255°C for 3 sec (5 sec max).
- 3. Do not apply stress to the epoxy resin while the temperature is above 85°C.
 4. Fixtures should not incur stress on the component when mounting and during soldering process.
 5. SAC 305 solder alloy is recommended.
- 6. No more than one wave soldering pass.

PACKING & LABEL SPECIFICATIONS

